

Hiroshi Inokawa

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/6533684/publications.pdf>

Version: 2024-02-01

162
papers

2,847
citations

218381

26
h-index

197535

49
g-index

164
all docs

164
docs citations

164
times ranked

1969
citing authors

#	ARTICLE	IF	CITATIONS
1	FDTD Study on Evolution of Trimer Silver@Silica Nanospheres to Dimer for SERS Characteristics. Plasmonics, 2022, 17, 647-652.	1.8	3
2	High-frequency rectifying characteristics of metallic single-electron transistor with niobium nanodots. Japanese Journal of Applied Physics, 2022, 61, SC1063.	0.8	4
3	Responsivity and NEP Improvement of Terahertz Microbolometer by High-Impedance Antenna. Sensors, 2022, 22, 5107.	2.1	3
4	Noncontact Characterization Techniques of GaN-Based Terahertz Devices. Lecture Notes in Electrical Engineering, 2021, , 29-42.	0.3	0
5	Design and Development of Terahertz Medical Screening Devices. Lecture Notes in Electrical Engineering, 2021, , 395-404.	0.3	4
6	Terahertz Radiation from Gallium Phosphide Avalanche Transit Time Sources. , 2021, , 49-58.		1
7	Tunable graphene nanopatch antenna design for on-chip integrated terahertz detector arrays with potential application in cancer imaging. Nanomedicine, 2021, 16, 1035-1047.	1.7	19
8	Real-time FPGA-based signal processing for silicon-on-insulator MOSFET single-photon detector: study on photon number statistics. Japanese Journal of Applied Physics, 2021, 60, 092004.	0.8	1
9	Measurement of thermal conductivity and thermal diffusivity of one-dimensional-system material by scanning electron microscopy and infrared thermography. AIP Advances, 2021, 11, .	0.6	1
10	Substrate Bias Effect on SOI-based Thermoelectric Power Generator. , 2021, , .		0
11	Responsivity Calibration of Terahertz Pyroelectric Detector Based on Blackbody Radiator. , 2021, , .		0
12	Angle-Sensitive Detector Based on Silicon-On-Insulator Photodiode Stacked with Surface Plasmon Antenna. Sensors, 2020, 20, 5543.	2.1	6
13	Polarization Dependence Of Incident Angle Sensitivity In Soi Photodiode With 2d Hole Array Grating. , 2020, , .		0
14	Performance Comparison of SOI-Based Temperature Sensors for Room-Temperature Terahertz Antenna-Coupled Bolometers: MOSFET, PN Junction Diode and Resistor. Micromachines, 2020, 11, 718.	1.4	12
15	Angular selectivity of SOI photodiode with surface plasmon antenna. IEICE Electronics Express, 2020, 17, 20200187-20200187.	0.3	5
16	Investigation of silicon-on-insulator CMOS integrated thermocouple and heater for antenna-coupled bolometer. Japanese Journal of Applied Physics, 2019, 58, SDDE08.	0.8	2
17	Performance improvement of on-chip integrable terahertz microbolometer arrays using nanoscale meander titanium thermistor. Journal of Applied Physics, 2019, 125, .	1.1	21
18	Synthesis of Triâ€functional Coreâ€shell CuO@carbon Quantum Dots@carbon Hollow Nanospheres Heterostructure for Nonâ€enzymatic H 2 O 2 Sensing and Overall Water Splitting Applications. Electroanalysis, 2019, 31, 2120-2129.	1.5	6

#	ARTICLE	IF	CITATIONS
19	Development of carbon coated NiS ₂ as positive electrode material for high performance asymmetric supercapacitor. Composites Part B: Engineering, 2019, 177, 107373.	5.9	72
20	Optimization of electric field enhancement of Ag@SiO ₂ trimer nanospheres by finite difference time domain method. Applied Surface Science, 2019, 495, 143547.	3.1	12
21	Optimization of active surface area of flower like MoS ₂ using V-doping towards enhanced hydrogen evolution reaction in acidic and basic medium. Applied Catalysis B: Environmental, 2019, 254, 432-442.	10.8	185
22	Directivity of SOI Photodiode with Gold Surface Plasmon Antenna. , 2019, , .		1
23	Comparative Study on 1-THz Antenna-Coupled Bolometer with Various SOI-CMOS based Temperature Sensors: MOSFET, Diode, Resistor and Thermocouple. , 2019, , .		0
24	Impact of Downscaling on Terahertz Antenna-Coupled Bolometers. , 2019, , .		2
25	Room-Temperature Terahertz Antenna-Coupled Microbolometers with Titanium Thermistor and Heater. , 2019, , .		1
26	High Responsivity and Low NEP of Room-Temperature Terahertz Antenna-Coupled Microbolometers with Meander Titanium Thermistor. , 2019, , .		2
27	A SILAR method for the fabrication of layer-by-layer assembled Cu ₂ O-reduced graphene oxide composite for non-enzymatic detection of hydrogen peroxide. Materials Research Express, 2019, 6, 025045.	0.8	4
28	Optimization of narrow width effect on titanium thermistor in uncooled antenna-coupled terahertz microbolometer. Japanese Journal of Applied Physics, 2018, 57, 04FC09.	0.8	16
29	Modified electrochemical charge storage properties of h-BN/rGO superlattice through the transition from n to p type semiconductor by fluorine doping. Chemical Engineering Journal, 2018, 339, 334-345.	6.6	27
30	Characterization of platinum and titanium thermistors for terahertz antenna-coupled bolometer applications. Sensors and Actuators A: Physical, 2018, 273, 49-57.	2.0	24
31	Novel synthesis of a Cu ₂ O-graphene nanoplatelet composite through a two-step electrodeposition method for selective detection of hydrogen peroxide. New Journal of Chemistry, 2018, 42, 3574-3581.	1.4	21
32	Modeling, Simulation, Fabrication, and Characterization of a 10^{14} W/cm ² Class Si-Nanowire Thermoelectric Generator for IoT Applications. IEEE Transactions on Electron Devices, 2018, 65, 5180-5188.	1.6	54
33	10^{14} W/cm ² -Class High Power Density Planar Si-Nanowire Thermoelectric Energy Harvester Compatible with CMOS-VLSI Technology. , 2018, , .		7
34	Antenna-Coupled Terahertz Microbolometers with Meander Structures: the Comparison of Titanium and Platinum Thermistors. , 2018, , .		3
35	Ultrahigh-Frequency Characteristics of Single-Electron Transistor. , 2018, , .		6
36	Application of bow-tie surface plasmon antenna to silicon on insulator nanowire photodiode for enhanced light absorption. IEICE Electronics Express, 2018, 15, 20180328-20180328.	0.3	3

#	ARTICLE	IF	CITATIONS
37	1.0-THz GaN IMPATT Source: Effect of Parasitic Series Resistance. <i>Journal of Infrared, Millimeter, and Terahertz Waves</i> , 2018, 39, 954-974.	1.2	39
38	Width dependence of platinum and titanium thermistor characteristics for application in room-temperature antenna-coupled terahertz microbolometer. <i>Japanese Journal of Applied Physics</i> , 2017, 56, 04CC07.	0.8	21
39	Thermal conductance and heat capacity measurement utilizing suspended-wire resistor. , 2017, , .		0
40	Strong Quantum Confinement Effects in Nanometer Devices with Graphene Directly Grown on Insulator by Catalyst-free Chemical Vapor Deposition. <i>Current Graphene Science</i> , 2017, 1, .	0.5	0
41	Highly sensitive and functional photodetectors based on silicon-on-insulator. , 2016, , .		1
42	Fabrication and single-electron-transfer operation of a triple-dot single-electron transistor. <i>Journal of Applied Physics</i> , 2015, 118, .	1.1	6
43	Fabrication and analytical modeling of integrated heater and thermistor for antenna-coupled bolometers. <i>Sensors and Actuators A: Physical</i> , 2015, 222, 160-166.	2.0	17
44	Room-temperature THz antenna-coupled microbolometer with a Joule-heating resistor at the center of a half-wave antenna. , 2014, , .		10
45	Broadband absorption enhancement of thin SOI photodiode with high-density gold nanoparticles. <i>Optical Materials Express</i> , 2014, 4, 725.	1.6	6
46	Effects of substrate voltage on noise characteristics and hole lifetime in SOI metal-oxide-semiconductor field-effect transistor photon detector. <i>Optics Express</i> , 2014, 22, 22072.	1.7	2
47	Material Dependence of Metal Grating on SOI Photodiode for Enhanced Quantum Efficiency. <i>IEEE Photonics Technology Letters</i> , 2013, 25, 1133-1136.	1.3	9
48	Evolution of photodetectors by silicon-on-insulator material. , 2013, , .		0
49	Substrate bias effects on noise and minority carrier lifetime in SOI MOSFET single-photon detector. , 2013, , .		0
50	Enhanced Visible Light Sensitivity by Gold Line-and-Space Grating Gate Electrode in Thin Silicon-On-Insulator p-n Junction Photodiode. <i>IEEE Transactions on Electron Devices</i> , 2013, 60, 812-818.	1.6	12
51	Enhancement of SOI Photodiode Sensitivity by Aluminum Grating. <i>ECS Transactions</i> , 2013, 53, 127-130.	0.3	4
52	(Invited) High-Speed Operation of Si Single-Electron Transistor. <i>ECS Transactions</i> , 2013, 58, 73-80.	0.3	4
53	Analysis of Hole Lifetime in SOI MOSFET Single-Photon Detector. <i>MAKARA of Technology Series</i> , 2013, 17, .	0.0	0
54	Single-Photon Detection by a Simple Silicon-on-Insulator Metal-oxide-Semiconductor Field-Effect Transistor. <i>Japanese Journal of Applied Physics</i> , 2012, 51, 06FE01.	0.8	5

#	ARTICLE	IF	CITATIONS
55	Effect of Arrangement of Input Gates on Logic Switching Characteristics of Nanodot Array Device. IEICE Transactions on Electronics, 2012, E95.C, 865-870.	0.3	2
56	High-frequency properties of Si single-electron transistor. , 2012, , .		1
57	Optoelectrical lifetime evaluation of single holes in SOI MOSFET. , 2012, , .		0
58	A differential smoothing technique for the extraction of MOSFET threshold voltage using extrapolation in the linear region. Solid-State Electronics, 2012, 76, 5-7.	0.8	9
59	Surface Plasmon Antenna with Gold Line and Space Grating for Enhanced Visible Light Detection by a Silicon-on-Insulator Metalâ€“Oxideâ€“Semiconductor Photodiode. IEEE Nanotechnology Magazine, 2012, 11, 346-351.	1.1	12
60	Single-Photon Detection by a Simple Silicon-on-Insulator Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistor. Japanese Journal of Applied Physics, 2012, 51, 06FE01.	0.8	6
61	Single-photon detection by SOI MOSFET. , 2011, , .		0
62	SOI metal-oxide-semiconductor field-effect transistor photon detector based on single-hole counting. Optics Letters, 2011, 36, 2800.	1.7	16
63	è¡“éćăf—ăf ©ă,°ăf ćăf³ă,¹ă`©ç””ă—ăŷă...%œœă†ă™”ă@æ€Sèf1/2ăăš. Hyomen Gijutsu/Journal of the Surface Finishing Society of Japan		
64	Electrical Characterization of Terphenyl-Based Molecular Devices. Japanese Journal of Applied Physics, 2011, 50, 071603.	0.8	0
65	Sensitivity improvement of silicon-on-insulator photodiode by gold nanoparticles with substrate bias control. Applied Physics Letters, 2011, 99, .	1.5	7
66	Si Nanodot Device Fabricated by Thermal Oxidation and their Applications. Key Engineering Materials, 2011, 470, 175-183.	0.4	0
67	Single-Photon Detector Based on MOSFET Electrometer with Single-Electron Sensitivity. Advanced Materials Research, 2011, 222, 3-7.	0.3	2
68	Electrical Characterization of Terphenyl-Based Molecular Devices. Japanese Journal of Applied Physics, 2011, 50, 071603.	0.8	1
69	Fabrication of double-dot single-electron transistor in silicon nanowire. Thin Solid Films, 2010, 518, S186-S189.	0.8	7
70	Evaluation of adhesion materials for gold line-and-space surface plasmon antenna on SOI-MOS photodiode. , 2010, , .		2
71	Effect of oxide thickness on the low-frequency noise in MOSFET-based charge transfer devices. , 2010, , .		1
72	Fabrication Method of Sub-100 nm Metalâ€“Oxideâ€“Semiconductor Field-Effect Transistor with Thick Gate Oxide. Japanese Journal of Applied Physics, 2010, 49, 128002.	0.8	4

#	ARTICLE	IF	CITATIONS
73	Low Frequency Noise Characterization in Metal Oxide Semiconductor Field Effect Transistor Based Charge Transfer Device at Room and Low Temperatures. Japanese Journal of Applied Physics, 2010, 49, 034203.	0.8	2
74	Geometrical effect in submicrometer channel organic field effect transistors. Thin Solid Films, 2009, 518, 579-582.	0.8	1
75	Single-Electron Device With Si Nanodot Array and Multiple Input Gates. IEEE Nanotechnology Magazine, 2009, 8, 535-541.	1.1	13
76	Electromagnetic testing and image reconstruction with flexible scanning tablets. , 2009, , .		1
77	Silicon Single-Electron Devices. Nanostructure Science and Technology, 2009, , 125-172.	0.1	23
78	Full Adder Operation Based on Si Nanodot Array Device with Multiple Inputs and Outputs. International Journal of Nanotechnology and Molecular Computation, 2009, 1, 58-69.	0.3	2
79	Charge transport in boron-doped nano MOSFETs: Towards single-dopant electronics. Applied Surface Science, 2008, 254, 6252-6256.	3.1	6
80	Silicon nanodot-array device with multiple gates. Materials Science in Semiconductor Processing, 2008, 11, 175-178.	1.9	5
81	Silicon single-charge transfer devices. Journal of Physics and Chemistry of Solids, 2008, 69, 702-707.	1.9	2
82	Pauli-spin-blockade transport through a silicon double quantum dot. Physical Review B, 2008, 77, .	1.1	115
83	Enhancement of light absorption by Au L/S grating for thin SOI photodetector. , 2008, , .		0
84	Single-Electron-Resolution Electrometer Based on Field-Effect Transistor. Japanese Journal of Applied Physics, 2008, 47, 8305-8310.	0.8	30
85	Full adder operation based on Si nanodot array device. , 2008, , .		0
86	Why the long-term charge offset drift in Si single-electron tunneling transistors is much smaller (better) than in metal-based ones: Two-level fluctuator stability. Journal of Applied Physics, 2008, 104, .	1.1	43
87	A gate-defined silicon quantum dot molecule. Applied Physics Letters, 2008, 92, 222104.	1.5	33
88	Stochastic data processing circuit based on single electrons using nanoscale field-effect transistors. Applied Physics Letters, 2008, 92, 062105.	1.5	22
89	Direct Measurement of Capacitance Parameters in Nanometer-Scale MOSFETs. IEEJ Transactions on Electronics, Information and Systems, 2008, 128, 905-911.	0.1	0
90	Field-Effect Transistor with Deposited Graphite Thin Film. Japanese Journal of Applied Physics, 2007, 46, 2615-2617.	0.8	4

#	ARTICLE	IF	CITATIONS
91	Long Retention of Gain-Cell Dynamic Random Access Memory With Undoped Memory Node. IEEE Electron Device Letters, 2007, 28, 48-50.	2.2	6
92	Effect of UV/Ozone Treatment on Nanogap Electrodes for Molecular Devices. Japanese Journal of Applied Physics, 2007, 46, 1731-1733.	0.8	3
93	Infrared detection with silicon nano-field-effect transistors. Applied Physics Letters, 2007, 90, 223108.	1.5	17
94	Charge offset stability in tunable-barrier Si single-electron tunneling devices. Applied Physics Letters, 2007, 90, 033507.	1.5	34
95	Mechanism of metal-semiconductor transition in electric properties of single-walled carbon nanotubes induced by low-energy electron irradiation. Journal of Applied Physics, 2007, 101, 034317.	1.1	27
96	Conductance modulation by individual acceptors in Si nanoscale field-effect transistors. Applied Physics Letters, 2007, 90, 102106.	1.5	90
97	Impact of Space-Energy Correlation on Variable Range Hopping in a Transistor. Physical Review Letters, 2007, 98, 166601.	2.9	4
98	Quantized electron transfer through random multiple tunnel junctions in phosphorus-doped silicon nanowires. Physical Review B, 2007, 76, .	1.1	54
99	Fast all-optical switching using ion-implanted silicon photonic crystal nanocavities. Applied Physics Letters, 2007, 90, 031115.	1.5	155
100	Resistance Ridges Along Filling Factor $\hat{1}/2 = 4i$ in SiO ₂ /Si/SiO ₂ Quantum Wells. AIP Conference Proceedings, 2007, , .	0.3	0
101	Transfer and Detection of Single Electrons Using Metal-Oxide-Semiconductor Field-Effect Transistors. IEICE Transactions on Electronics, 2007, E90-C, 943-948.	0.3	5
102	A High-Density Ternary Content-Addressable Memory Using Single-Electron Transistors. , 2006, , .		4
103	Studies on Metal-oxide-Semiconductor Field-Effect Transistor Low-Frequency Noise for Electrometer Applications. Japanese Journal of Applied Physics, 2006, 45, 3606-3608.	0.8	4
104	Molecular-Mediated Single-Electron Devices Operating at Room Temperature. Japanese Journal of Applied Physics, 2006, 45, 4285-4289.	0.8	6
105	Room-temperature-operating data processing circuit based on single-electron transfer and detection with metal-oxide-semiconductor field-effect transistor technology. Applied Physics Letters, 2006, 88, 183101.	1.5	64
106	Electrostatically gated Si devices: Coulomb blockade and barrier capacitance. Applied Physics Letters, 2006, 89, 052102.	1.5	13
107	Single electron tunneling transistor with tunable barriers using silicon nanowire metal-oxide-semiconductor field-effect transistor. Applied Physics Letters, 2006, 88, 053121.	1.5	111
108	Single-electron device using Si nanodot array and multi-input gates. , 2006, , .		3

#	ARTICLE	IF	CITATIONS
109	Quantum effects in the capacitance between a pair of thin and slightly separated SrTiO ₃ slabs: A first-principles study. <i>Physical Review B</i> , 2006, 74, .	1.1	9
110	Impurity conduction in phosphorus-doped buried-channel silicon-on-insulator field-effect transistors at temperatures between 10 and 295K. <i>Physical Review B</i> , 2006, 74, .	1.1	15
111	Fast All-Optical Pulse Train Modulation by Silicon Photonic Crystal Nanocavities. , 2006, , .		1
112	Special Section on Novel Device Architectures and System Integration Technologies. <i>IEICE Transactions on Electronics</i> , 2006, E89-C, 1491-1491.	0.3	0
113	Charge-State Control of Phosphorus Donors in Silicon-on-Insulator Metal-Oxide-Semiconductor Field-Effect Transistor. <i>Japanese Journal of Applied Physics</i> , 2005, 44, 2588-2591.	0.8	9
114	Back-Gate Effect on Coulomb Blockade in Silicon-on-Insulator Trench Wires. <i>Japanese Journal of Applied Physics</i> , 2005, 44, 7717-7719.	0.8	8
115	Foundry Metal-oxide-semiconductor Field-Effect-Transistor Electrometer for Single-Electron Detection. <i>Japanese Journal of Applied Physics</i> , 2005, 44, 4855-4858.	0.8	7
116	Charge-Injection Effects in a Single 4,4''-Terphenyldithiol Molecule. <i>Japanese Journal of Applied Physics</i> , 2005, 44, 8759-8763.	0.8	6
117	Silicon Single-Electron Pump and Turnstile: Interplay with Crystalline Imperfections. <i>Materials Research Society Symposia Proceedings</i> , 2005, 864, 671.	0.1	1
118	Metal-semiconductor Transition in Single-Walled Carbon Nanotubes Induced by Low-Energy Electron Irradiation. <i>Nano Letters</i> , 2005, 5, 1575-1579.	4.5	87
119	Manipulation and detection of single electrons for future information processing. <i>Journal of Applied Physics</i> , 2005, 97, 031101.	1.1	112
120	First-Principles Study of Field-Effect Doping in Nano-Scale Systems by the Enforced Fermi-Energy Difference Method. <i>E-Journal of Surface Science and Nanotechnology</i> , 2005, 3, 453-456.	0.1	3
121	Simultaneous-Sweep Method for Evaluation of Single-Electron Transistors with Barriers Induced by Gate Electric Field. <i>Japanese Journal of Applied Physics</i> , 2004, 43, L1048-L1050.	0.8	8
122	Analysis of Back-Gate Voltage Dependence of Threshold Voltage of Thin Silicon-on-Insulator Metal-Oxide-Semiconductor Field-Effect Transistor and Its Application to Si Single-Electron Transistor. <i>Japanese Journal of Applied Physics</i> , 2004, 43, 2036-2040.	0.8	18
123	Multilevel memory using an electrically formed single-electron box. <i>Applied Physics Letters</i> , 2004, 85, 1277-1279.	1.5	31
124	Multilevel memory using single-electron turnstile. <i>Electronics Letters</i> , 2004, 40, 229.	0.5	14
125	Automatic Control of Oscillation Phase of a Single-Electron Transistor. <i>IEEE Electron Device Letters</i> , 2004, 25, 31-33.	2.2	8
126	A multiple-valued logic and memory with combined single-electron and metal-oxide-semiconductor transistors. <i>IEEE Transactions on Electron Devices</i> , 2003, 50, 462-470.	1.6	106

#	ARTICLE	IF	CITATIONS
127	A compact analytical model for asymmetric single-electron tunneling transistors. IEEE Transactions on Electron Devices, 2003, 50, 455-461.	1.6	89
128	Correction to "A compact analytical model for asymmetric single-electron tunneling transistors". IEEE Transactions on Electron Devices, 2003, 50, 862-862.	1.6	1
129	Development of silicon single-electron devices. Physica E: Low-Dimensional Systems and Nanostructures, 2003, 19, 95-101.	1.3	7
130	A Merged Single-Electron Transistor and Metal-Oxide-Semiconductor Transistor Logic for Interface and Multiple-Valued Functions. Japanese Journal of Applied Physics, 2002, 41, 2566-2568.	0.8	25
131	Silicon single-electron devices. Journal of Physics Condensed Matter, 2002, 14, R995-R1033.	0.7	111
132	Binary adders of multigate single-electron transistors: specific design using pass-transistor logic. IEEE Nanotechnology Magazine, 2002, 1, 93-99.	1.1	40
133	Silicon Single-Electron Transistors and Single-Electron CCD. Materials Research Society Symposia Proceedings, 2001, 686, 1.	0.1	0
134	Multipeak negative-differential-resistance device by combining single-electron and metal-oxide-semiconductor transistors. Applied Physics Letters, 2001, 79, 3618-3620.	1.5	49
135	A 0.5-V MTCMOS/SIMOX logic gate. IEEE Journal of Solid-State Circuits, 1997, 32, 1604-1609.	3.5	20
136	Nitrogen in-situ doped poly buffer LOCOS: simple and scalable isolation technology for deep-submicron silicon devices. IEEE Transactions on Electron Devices, 1996, 43, 311-317.	1.6	7
137	Evaluation of a copper metallization process and the electrical characteristics of copper-interconnected quarter-micron CMOS. IEEE Transactions on Electron Devices, 1996, 43, 1206-1212.	1.6	51
138	A 4:1 MUX Circuit Using 1/4 Micron CMOS/SIMOX for High-Speed and Low-Power Applications. Japanese Journal of Applied Physics, 1996, 35, 902-905.	0.8	1
139	Sub-1/4-μm dual-gate CMOS technology using in-situ doped polysilicon for nMOS and pMOS gates. IEEE Transactions on Electron Devices, 1995, 42, 1583-1590.	1.6	8
140	Sub-1/4 μm Dual Gate CMOS Technology using In Situ Doped Polysilicons for N and PMOS Gates. , 1993, , .		1
141	Degradation and Recovery of Metal-Oxide-Semiconductor (MOS) Devices Stressed with Fowler-Nordheim (FN) Gate Current. Japanese Journal of Applied Physics, 1991, 30, 1931-1936.	0.8	4
142	Direct Determination of Interface Trapped Charges. Japanese Journal of Applied Physics, 1991, 30, L888-L890.	0.8	1
143	Electrical characterization of metal-insulator-semiconductor diodes fabricated from laser-ablated YBa ₂ Cu ₃ O _{7-x} yttria-stabilized zirconia films on Si substrates. Applied Physics Letters, 1991, 59, 2889-2891. ^{1.5}		20
144	Titanium silicide and titanium nitride formation by titanium-ion implantation for MOS LSI applications. Journal of Materials Research, 1991, 6, 1238-1247.	1.2	17

#	ARTICLE	IF	CITATIONS
145	Electrical Characterization of YBCO/YSZ/Si Diodes. , 1991, , .		0
146	A Complete Self-aligned-gate LID-MOS Technology. , 1988, , .		0
147	Film and interface properties of epitaxial metal/insulator/semiconductor systems formed by ionized cluster beam deposition. Surface Science, 1986, 168, 365-375.	0.8	13
148	Submicron MOSFETs with S/D Diffusions on a Field Insulator. , 1986, , .		1
149	Aluminium epitaxy on Si(111) and Si(100) using an ionized cluster beam. Thin Solid Films, 1985, 124, 179-184.	0.8	22
150	Al metallization by ionized-cluster beam deposition and epitaxy. Nuclear Instruments & Methods in Physics Research B, 1985, 7-8, 900-905.	0.6	8
151	Film deposition and buried layer formation by mass-analyzed ion beams. Nuclear Instruments & Methods in Physics Research B, 1985, 6, 439-446.	0.6	19
152	Observation of Initial Stage of Al Epitaxial Growth on Si(111) by Ionized Cluster Beam Deposition. Japanese Journal of Applied Physics, 1985, 24, L173-L174.	0.8	18
153	Ion beam deposition. Microelectronic Engineering, 1984, 2, 113-120.	1.1	0
154	Epitaxial growth of Al on Si(111) and Si(100) by ionized cluster beam. Journal of Applied Physics, 1984, 56, 2746-2750.	1.1	174
155	Vaporized-metal cluster formation and effect of kinetic energy of ionized clusters on film formation. Thin Solid Films, 1982, 92, 137-146.	0.8	47
156	A multiple-valued single-electron SRAM by the PADOX process. , 0, , .		5
157	Automatic control of the oscillation phase of a single-electron transistor by a memory node with a small MOSFET. , 0, , .		0
158	Silicon nano-devices and single-electron devices. , 0, , .		1
159	High-Efficiency SOI Photodetector Utilizing Surface Plasmon Resonance in Gold Corrugated Structure. Advanced Materials Research, 0, 222, 154-157.	0.3	1
160	Investigation of Adhesion Materials for Gold Line-and-Space Surface Plasmon Antenna on SOI-MOS Photodiode. Advanced Materials Research, 0, 222, 201-204.	0.3	2
161	Identification of double quantum dots in nanowire devices by single-gate sweeps. , 0, , .		1
162	Full Adder Operation Based on Si Nanodot Array Device with Multiple Inputs and Outputs. , 0, , 131-139.		0